Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

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Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

UMC2NT1, UMC3NT1, UMC5NT1

Preferred Devices

Dual Common Base-Collector Bias Resistor Transistors

NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base−emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the UMC2NT1 series, two complementary BRT devices are housed in the SOT−353 package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel
- Pb−Free Packages are Available

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted, common for Q_1 and Q_2, − minus sign for Q_1 (PNP) omitted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

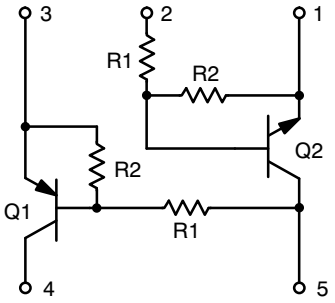
THERMAL CHARACTERISTICS

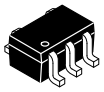
Thermal Resistance − Junction-to-Ambient (surface mounted)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range	T_J, T_{stg}	−65 to +150	°C
Total Package Dissipation @ T_A = 25°C (Note 1)	P_D	150	mW

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

ON Semiconductor®

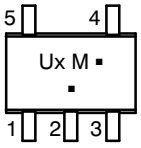
http://onsemi.com





SC−88A/SOT−353
CASE 419A
STYLE 6

MARKING DIAGRAM



Ux = Device Marking
x = 2, 3 or 5
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Q1 TRANSISTOR: PNP						
OFF CHARACTERISTICS						
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)		I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V_{CB} = 50 V, I_B = 0)		I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0, I_C = 0 mA)	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	I_{EBO}	– – –	– – –	0.2 0.5 1.0	mAdc
ON CHARACTERISTICS						
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)		$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)		$V_{(BR)CEO}$	50	–	–	Vdc
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	h_{FE}	60 35 20	100 60 35	– – –	
Collector–Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA)		$V_{CE(SAT)}$	–	–	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)		V_{OL}	–	–	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ)		V_{OH}	4.9	–	–	Vdc
Input Resistor	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	R1	15.4 7.0 3.3	22 10 4.7	28.6 13 6.1	kΩ
Resistor Ratio	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	R1/R2	0.8 0.8 0.38	1.0 1.0 0.47	1.2 1.2 0.56	
Q2 TRANSISTOR: NPN						
OFF CHARACTERISTICS						
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)		I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V_{CB} = 50 V, I_B = 0)		I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0, I_C = 0 mA)	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	I_{EBO}	– – –	– – –	0.2 0.5 0.1	mAdc
ON CHARACTERISTICS						
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)		$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)		$V_{(BR)CEO}$	50	–	–	Vdc
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	h_{FE}	60 35 80	100 60 140	– – –	
Collector–Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA)		$V_{CE(SAT)}$	–	–	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)		V_{OL}	–	–	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ)		V_{OH}	4.9	–	–	Vdc
Input Resistor	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	R1	15.4 7.0 33	22 10 47	28.6 13 61	kΩ
Resistor Ratio	UMC2NT1, G UMC3NT1, G UMC5NT1, G / T2, G	R1/R2	0.8 0.8 0.8	1.0 1.0 1.0	1.2 1.2 1.2	

ORDERING INFORMATION

Device	Package	Shipping†
UMC2NT1	SC−88A/SOT−353	3000 / Tape & Reel
UMC2NT1G	SC−88A/SOT−353 (Pb−Free)	3000 / Tape & Reel
UMC3NT1	SC−88A/SOT−353	3000 / Tape & Reel
UMC3NT1G	SC−88A/SOT−353 (Pb−Free)	3000 / Tape & Reel
UMC3NT2	SC−88A/SOT−353	3000 / Tape & Reel
UMC3NT2G	SC−88A/SOT−353 (Pb−Free)	3000 / Tape & Reel
UMC5NT1	SC−88A/SOT−353	3000 / Tape & Reel
UMC5NT1G	SC−88A/SOT−353 (Pb−Free)	3000 / Tape & Reel
UMC5NT2	SC−88A/SOT−353	3000 / Tape & Reel
UMC5NT2G	SC−88A/SOT−353 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Transistor 1 – PNP		Transistor 2 – NPN	
		R1 (K)	R2 (K)	R1 (K)	R2 (K)
UMC2NT1, G	U2	22	22	22	22
UMC3NT1, G	U3	10	10	10	10
UMC3NT2, G	U3	10	10	10	10
UMC5NT1, G	U5	4.7	10	47	47
UMC5NT2, G	U5	4.7	10	47	47

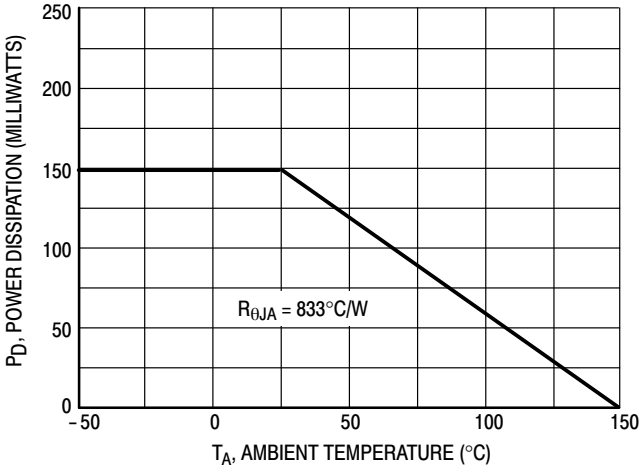


Figure 1. Derating Curve

TYPICAL ELECTRICAL CHARACTERISTICS — UMC2NT1 PNP TRANSISTOR

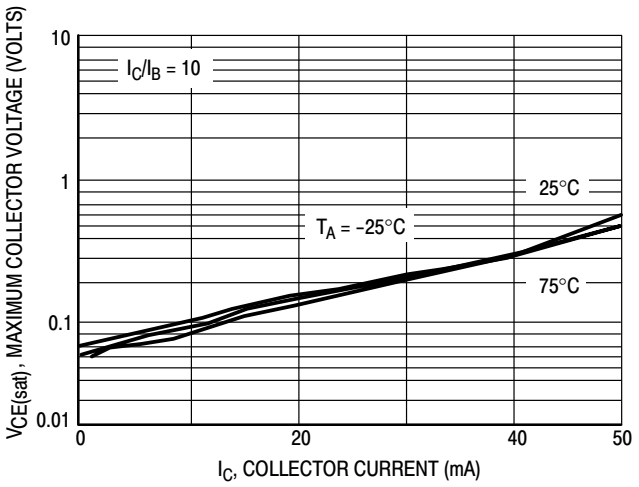


Figure 2. $V_{CE(sat)}$ versus I_C

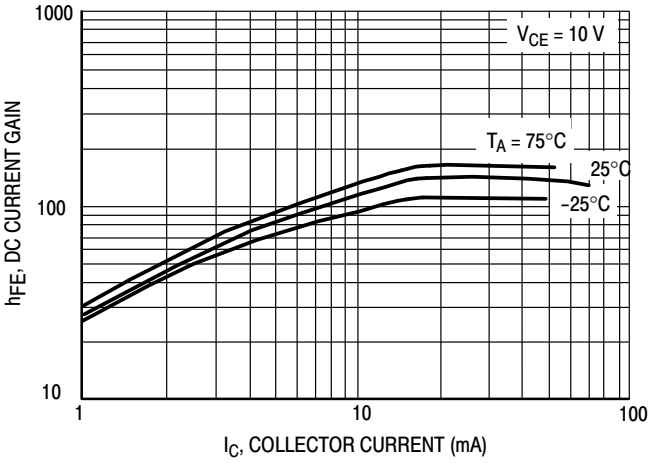


Figure 3. DC Current Gain

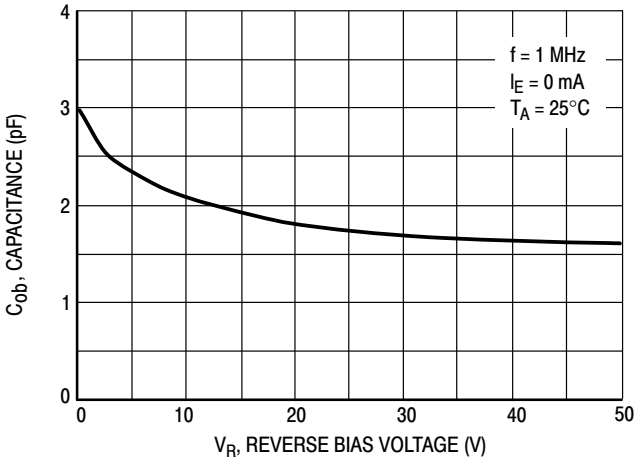


Figure 4. Output Capacitance

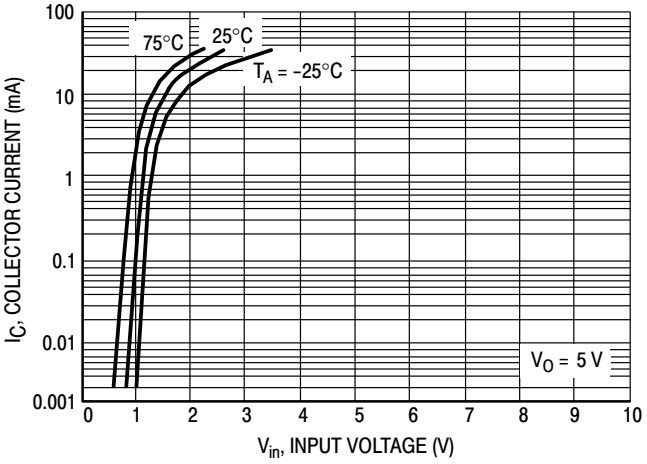


Figure 5. Output Current versus Input Voltage

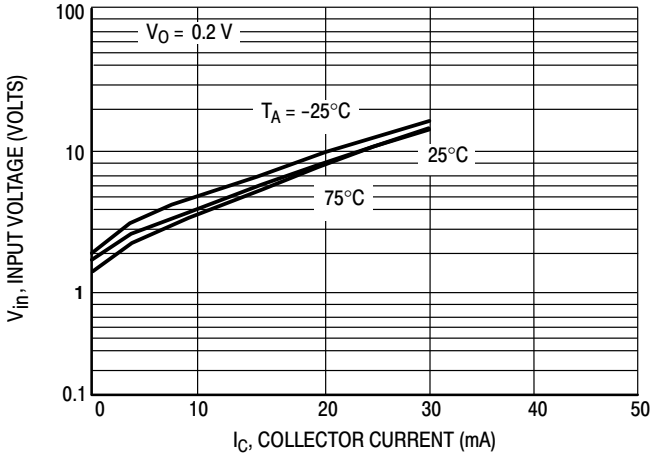


Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — UMC2NT1 NPN TRANSISTOR

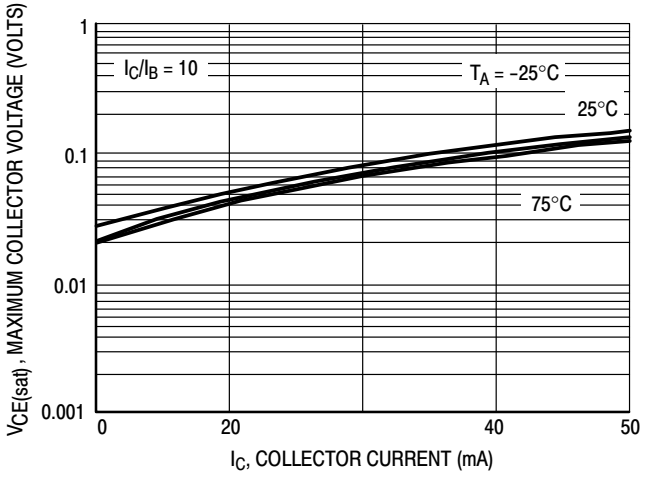


Figure 7. $V_{CE(sat)}$ versus I_C

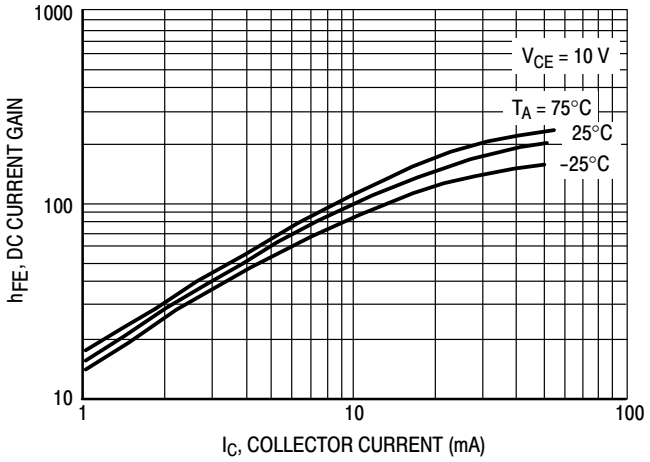


Figure 8. DC Current Gain

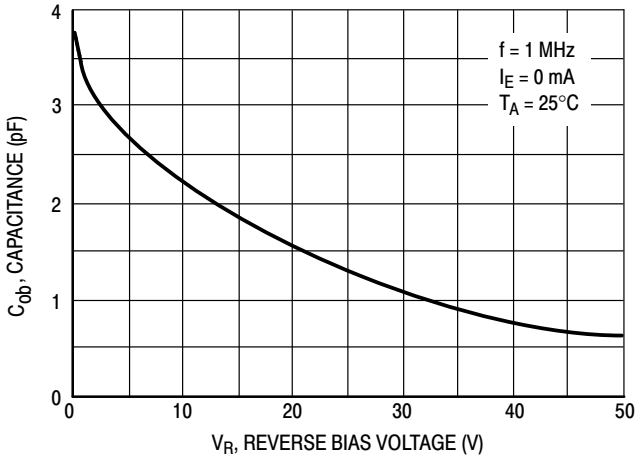


Figure 9. Output Capacitance

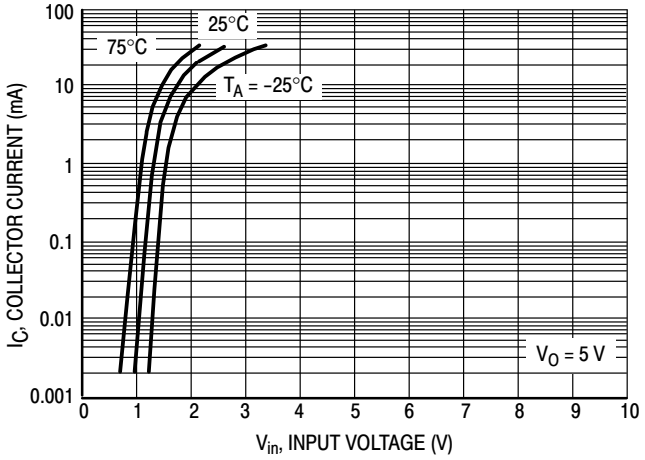


Figure 10. Output Current versus Input Voltage

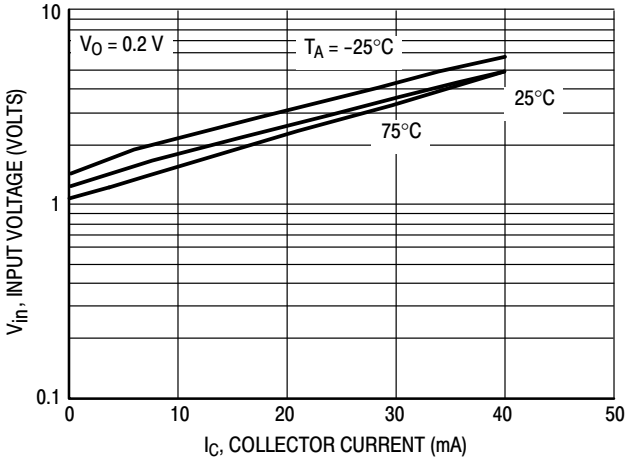


Figure 11. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — UMC3NT1 PNP TRANSISTOR

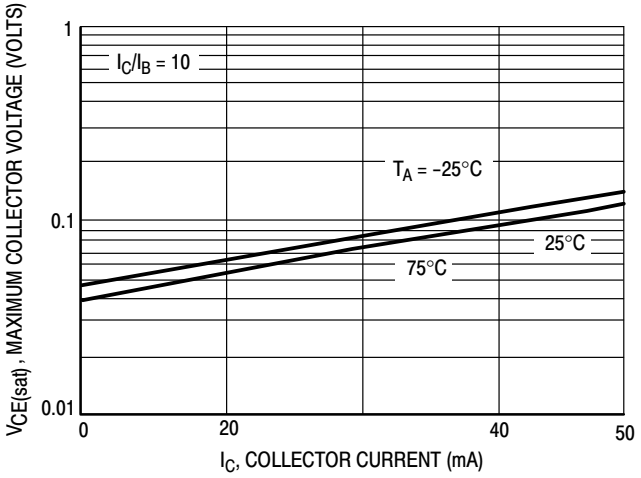


Figure 12. $V_{CE(sat)}$ versus I_C

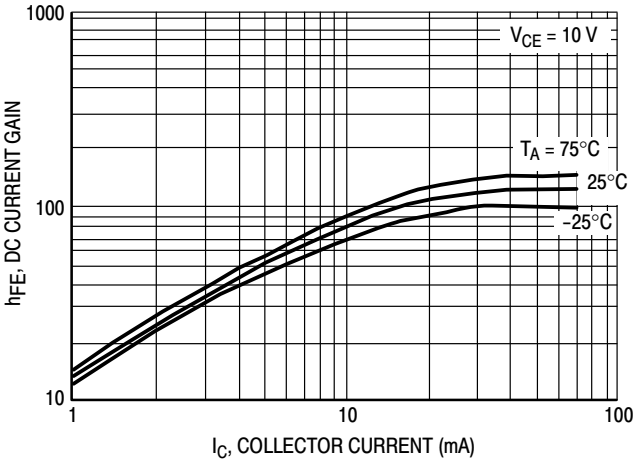


Figure 13. DC Current Gain

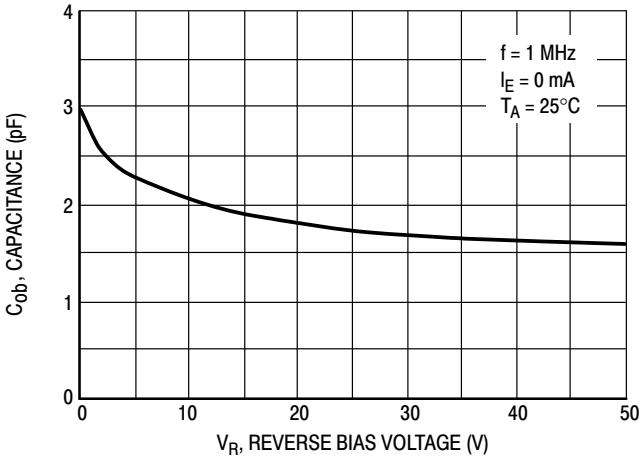


Figure 14. Output Capacitance

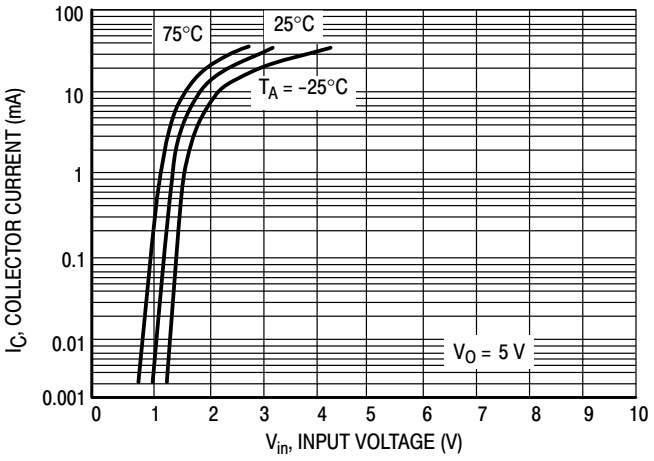


Figure 15. Output Current versus Input Voltage

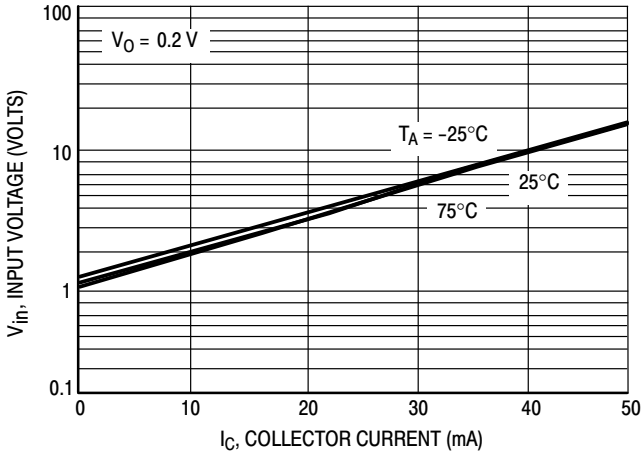


Figure 16. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — UMC3NT1 NPN TRANSISTOR

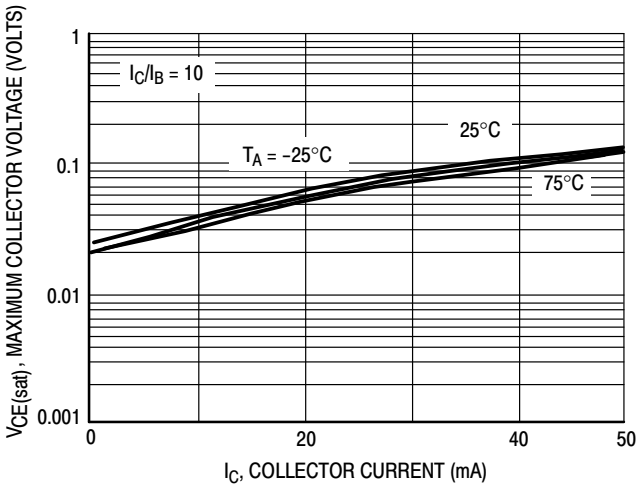


Figure 17. $V_{CE(sat)}$ versus I_C

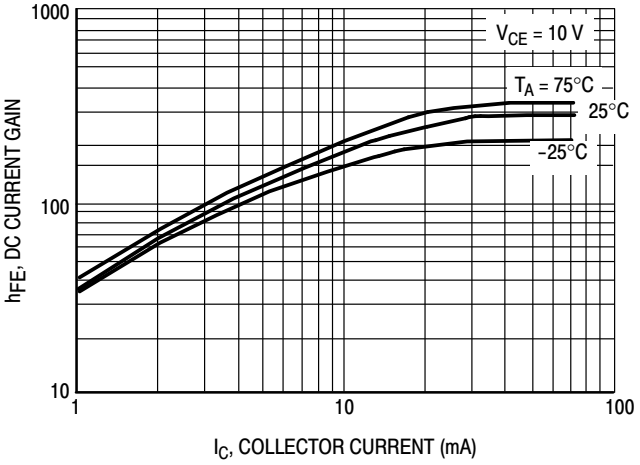


Figure 18. DC Current Gain

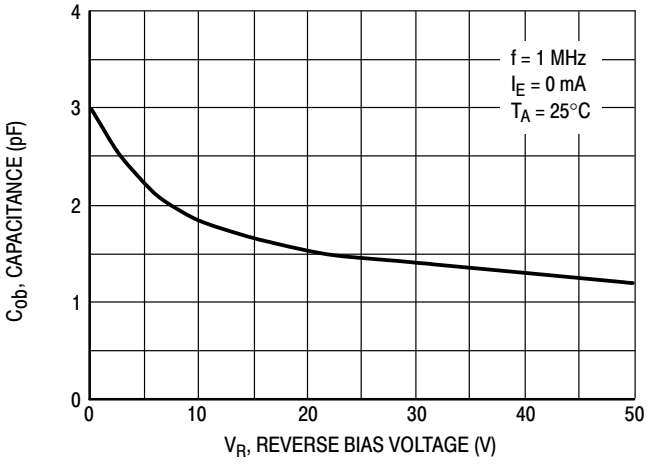


Figure 19. Output Capacitance

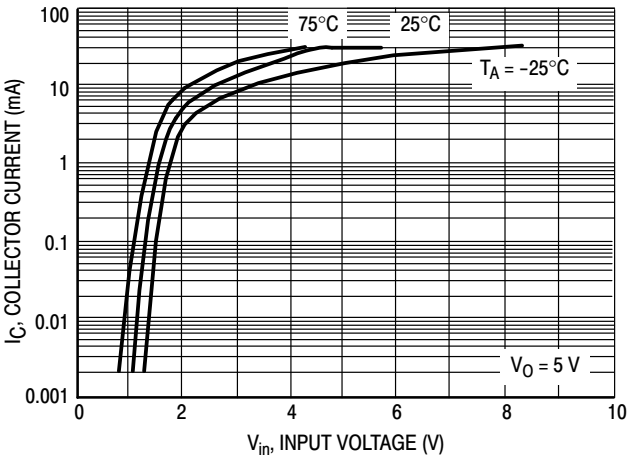


Figure 20. Output Current versus Input Voltage

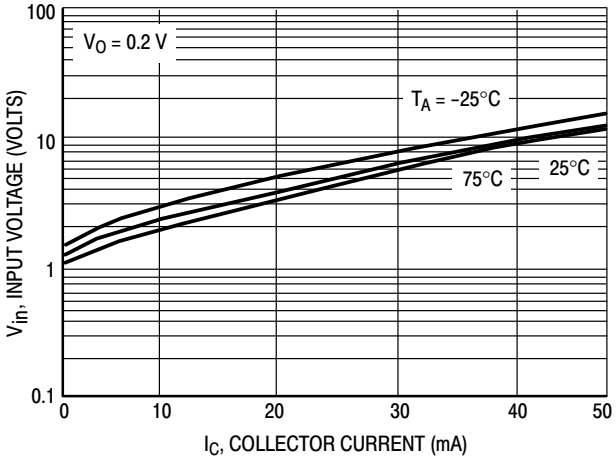


Figure 21. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — UMC5NT1 PNP TRANSISTOR

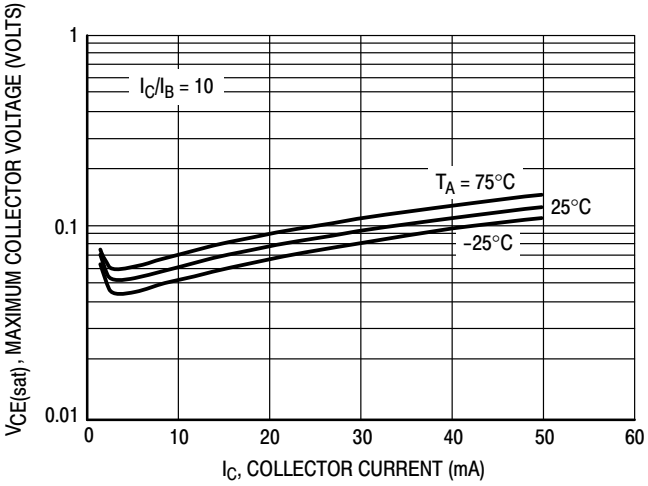


Figure 22. $V_{CE(sat)}$ versus I_C

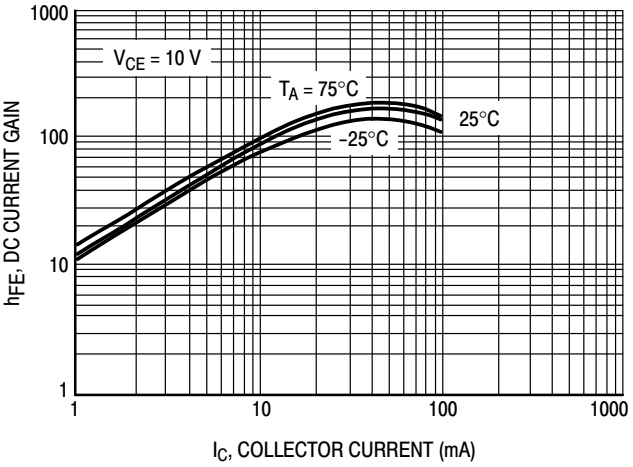


Figure 23. DC Current Gain

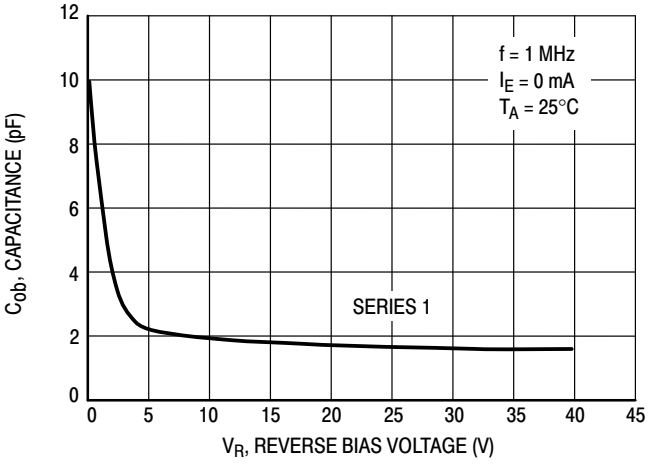


Figure 24. Output Capacitance

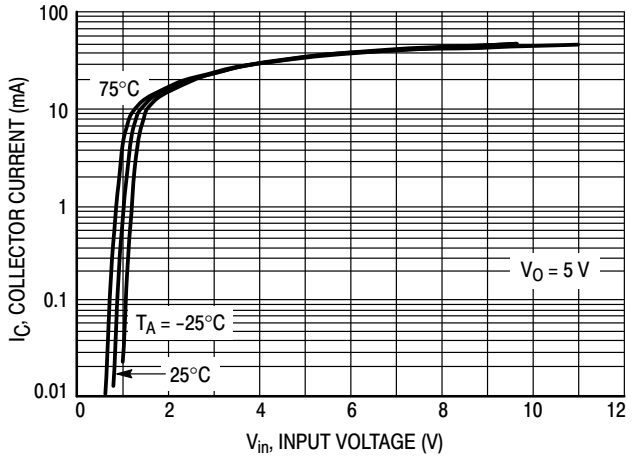


Figure 25. Output Current versus Input Voltage

TYPICAL ELECTRICAL CHARACTERISTICS — UMC5NT1 NPN TRANSISTOR

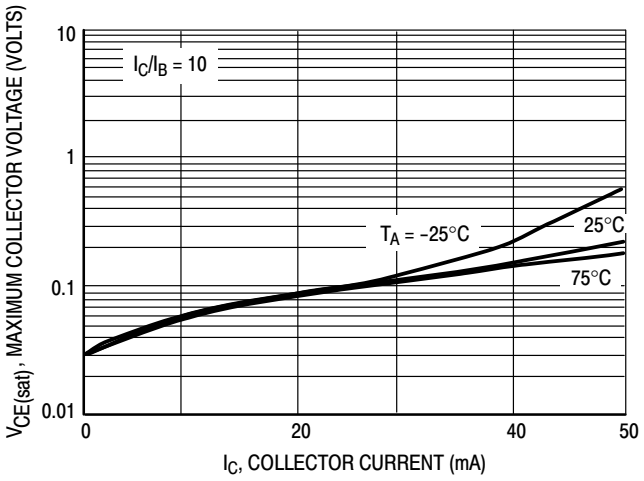


Figure 26. $V_{CE(sat)}$ versus I_C

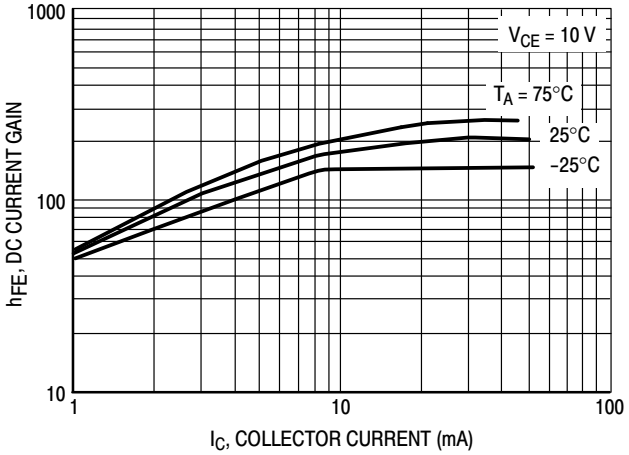


Figure 27. DC Current Gain

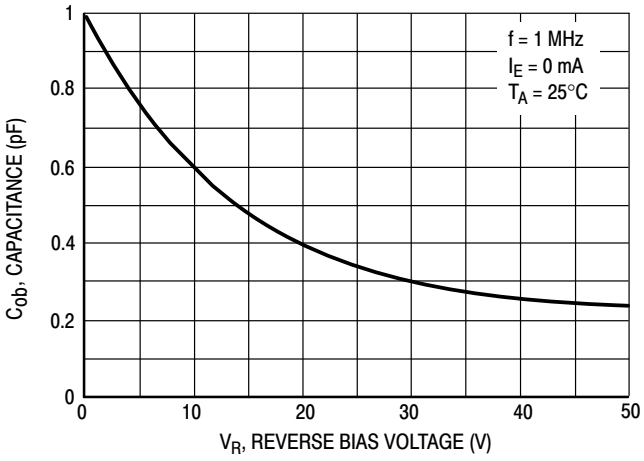


Figure 28. Output Capacitance

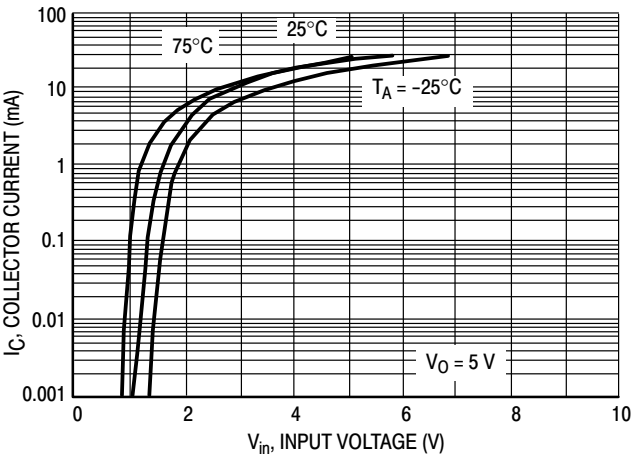


Figure 29. Output Current versus Input Voltage

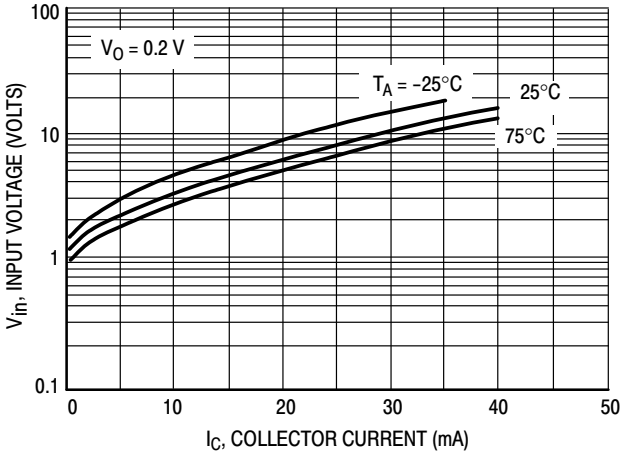
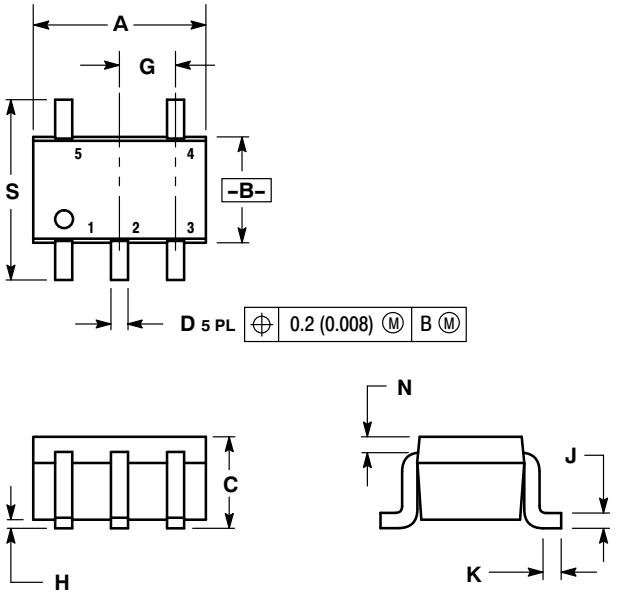


Figure 30. Input Voltage versus Output Current

PACKAGE DIMENSIONS

SC−88A, SOT−353, SC−70
CASE 419A−02
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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